

HM6287 Series

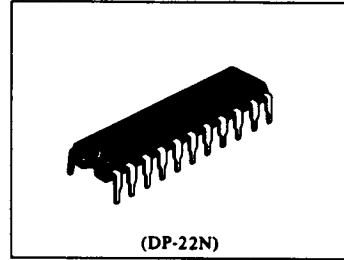
Maintenance Only

65536-word x 1-bit High Speed CMOS Static RAM

Refer to HM6287H Series

FEATURES

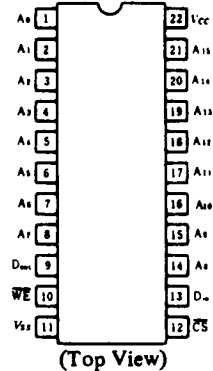
- High Speed: Fast Access Time 45/55/70ns (max.)
- Single 5V Supply and High Density 22 Pin Package
- Low Power Standby and Low Power Operation
Standby: 100 μ W (typ.)/10 μ W (typ.) (L-version)
Operation: 300mW (typ.)
- Completely Static Memory
No Clock or Timing Strobe Required
- Equal Access and Cycle Times
- Directly TTL Compatible: All Inputs and Output
- Capability of Battery Back Up Operation (L-version)



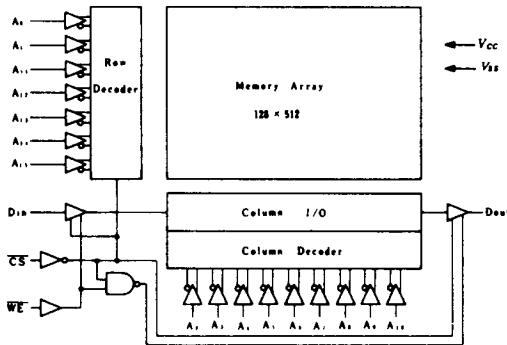
ORDERING INFORMATION

Type No.	Access Time	Package
HM6287P-45	45ns	300 mil 22 pin Plastic DIP
HM6287P-55	55ns	
HM6287P-70	70ns	
HM6287LP-45	45ns	300 mil 22 pin Plastic DIP
HM6287LP-55	55ns	
HM6287LP-70	70ns	

PIN ARRANGEMENT



BLOCK DIAGRAM



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■ TRUTH TABLE

CS	WE	Mode	V _{CC} Current	Dout Pin	Ref. Cycle
H	X	Not Selected	I _{SB} , I _{SB1}	High Z	–
L	H	Read	I _{CC}	Dout	Read Cycle
L	L	Write	I _{CC}	High Z	Write Cycle

■ ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Voltage on Any Pin Relative to V _{SS}	V _T	-0.5 ^{*1} to +7.0	V
Power Dissipation	P _T	1.0	W
Operating Temperature	T _{opr}	0 to +70	°C
Storage Temperature	T _{stg}	-55 to +125	°C
Temperature Under Bias	T _{bias}	-10 to +85	°C

Note) *1. -3.5V for pulse width ≤ 20ns

■ RECOMMENDED DC OPERATING CONDITIONS (T_a = 0 to +70°C)

Item	Symbol	min	typ	max	Unit
Supply Voltage	V _{CC}	4.5	5.0	5.5	V
	V _{SS}	0	0	0	V
Input Voltage	V _{IH}	2.2	–	6.0	V
	V _{IL}	-0.5 ^{*1}	–	0.8	V

Note) *1. -3.0V for pulse width ≤ 20ns

■ DC AND OPERATING CHARACTERISTICS (V_{CC} = 5V ± 10%, V_{SS} = 0V, T_a = 0 to +70°C)

Item	Symbol	Test Conditions	min	typ ^{*1}	max	Unit
Input Leakage Current	I _{LI}	V _{CC} = 5.5V, V _{in} = V _{SS} to V _{CC}	–	–	2.0	μA
Output Leakage Current	I _{LO}	CS = V _{IH} , V _{out} = V _{SS} to V _{CC}	–	–	2.0	μA
Operating Power Supply Current	I _{CC}	CS = V _{IL} , I _{out} = 0mA, min. cycle	–	60	100	mA
	I _{SB}	CS = V _{IH} , min. cycle	–	10	30	mA
Standby Power Supply Current	I _{SB1}	CS ≥ V _{CC} - 0.2V, 0V ≤ V _{in} ≤ 0.2V or V _{CC} - 0.2V ≤ V _{in}	–	0.02	2.0	mA
	I _{OL}	I _{OL} = 8mA	–	2 ^{*2}	100 ^{*2}	μA
Output Voltage	V _{OL}	I _{OL} = 8mA	–	–	0.4	V
	V _{OH}	I _{OH} = -4.0mA	2.4	–	–	V

Notes) *1. Typical limits are at V_{CC} = 5.0V, T_a = 25°C and specified loading.
*2. This characteristics is guaranteed only for L-version.

■ CAPACITANCE (f = 1MHz, T_a = 25°C)

Item	Symbol	Test Conditions	min	typ	max	Unit
Input Capacitance	C _{in}	V _{in} = 0V	–	–	5	pF
Output Capacitance	C _{out}	V _{out} = 0V	–	–	7.5	pF

Note) This parameter is sampled and not 100% tested.

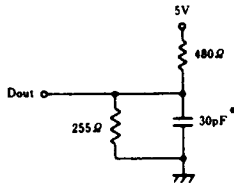


■ AC CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_a = 0$ to $+70^\circ\text{C}$, unless otherwise noted)

● AC TEST CONDITIONS

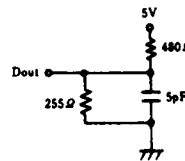
- Input Pulse Levels: V_{SS} to 3.0V
- Input Rise and Fall Times: 5ns
- Input and Output Timing Reference Levels: 1.5V
- Output Load: See Figure

Output Load A



*Including scope & jig capacitance

Output Load B

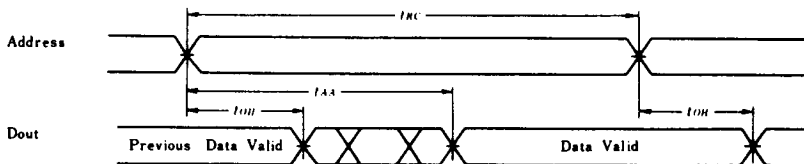


*Including scope & jig capacitance

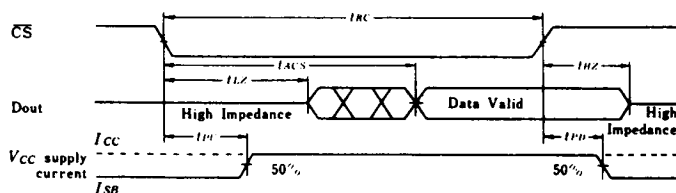
● READ CYCLE

Item	Symbol	HM6287-45		HM6287-55		HM6287-70		Unit	Notes
		min	max	min	max	min	max		
Read Cycle Time	t_{RC}	45	—	55	—	70	—	ns	1
Address Access Time	t_{AA}	—	45	—	55	—	70	ns	
Chip Select Access Time	t_{ACS}	—	45	—	55	—	70	ns	
Output Hold from Address Change	t_{OH}	5	—	5	—	5	—	ns	
Chip Selection to Output in Low Z	t_{LZ}	5	—	5	—	5	—	ns	2, 3, 7
Chip Deselection to Output in High Z	t_{HZ}	0	30	0	30	0	30	ns	2, 3, 7
Chip Selection to Power Up Time	t_{PU}	0	—	0	—	0	—	ns	7
Chip Deselection to Power Down Time	t_{PD}	—	40	—	40	—	40	ns	7

● Timing Waveform of Read Cycle No. 1⁽⁴⁾⁽⁵⁾



● Timing Waveform of Read Cycle No. 2⁽⁴⁾⁽⁶⁾



- Notes:
1. All Read Cycle timings are referenced from last valid address to the first transitioning address.
 2. At any given temperature and voltage condition, t_{HZ} max. is less than t_{LZ} min. both for a given device and from device to device.
 3. Transition is measured ± 500 mV from steady state voltage with specified loading in Load B.
 4. \overline{WE} is high for READ Cycle.
 5. Device is continuously selected, while $\overline{CS} = V_{IL}$.
 6. Address valid prior to or coincident with \overline{CS} transition low.
 7. This parameter is sampled and not 100% tested.

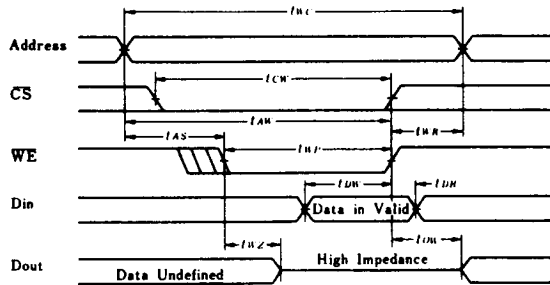


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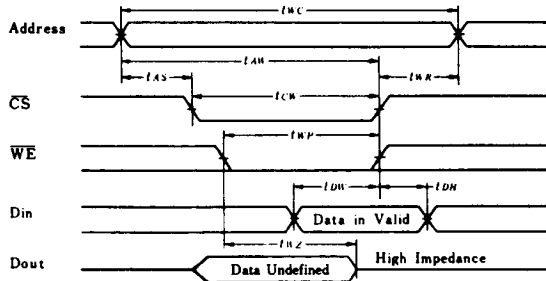
● WRITE CYCLE

Item	Symbol	HM6287-45		HM6287-55		HM6287-70		Unit	Notes
		min	max	min	max	min	max		
Write Cycle Time	t_{WC}	45	—	55	—	70	—	ns	2
Chip Selection to End of Write	t_{CW}	40	—	50	—	55	—	ns	
Address Valid to End of Write	t_{AW}	40	—	50	—	55	—	ns	
Address Setup Time	t_{AS}	0	—	0	—	0	—	ns	
Write Pulse Width	t_{WP}	25	—	35	—	40	—	ns	
Write Recovery Time	t_{WR}	0	—	0	—	0	—	ns	
Data Valid to End of Write	t_{DW}	25	—	25	—	30	—	ns	
Data Hold Time	t_{DH}	0	—	0	—	0	—	ns	
Write Enabled to Output in High Z	t_{WZ}	0	25	0	25	0	30	ns	3, 4
Output Active from End of Write	t_{OW}	0	—	0	—	0	—	ns	3, 4

● Timing Waveform of Write Cycle No. 1 (\overline{WE} Controlled)



● Timing Waveform of Write Cycle No. 1 (\overline{CS} Controlled)



- Notes)
1. If \overline{CS} goes high Simultaneously with \overline{WE} high, the output remains in a high impedance state.
 2. All Write Cycle timings are referenced from the last valid address to the first transitioning address.
 3. Transition is measured $\pm 500\text{mV}$ from steady state voltage with specified loading in Load B.
 4. This parameter is sampled and not 100% tested.



■ **LOW V_{CC} DATA RETENTION CHARACTERISTICS** ($T_a = 0$ to $+70^\circ\text{C}$)

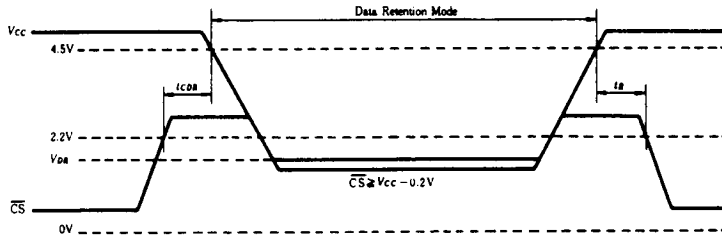
This characteristics is guaranteed only for L-version.

Parameter	Symbol	Test Condition	min.	typ.	max.	Unit
V_{CC} for Data Retention	V_{DR}	$CS \geq V_{CC} - 0.2V$, $V_{ip} \leq V_{CC} - 0.2V$ or $0V \leq V_{in} \leq 0.2V$	2.0	-	-	V
Data Retention Current	I_{CCDR}	See retention wave- form	-	1	50^{*2}	μA
Chip Deselect to Data Retention Time	t_{CDR}		0	-	-	ns
Operation Recovery Time	t_R		t_{RC}^{*1}	-	-	ns

Note) *1. t_{RC} = Read Cycle Time

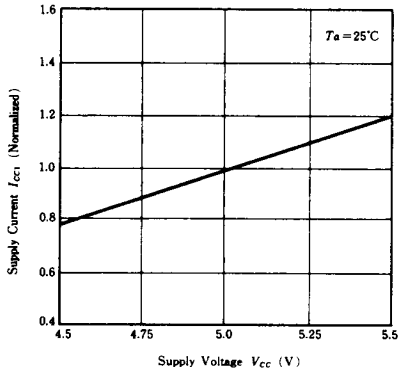
*2. $V_{CC} = 3.0V$

● **LOW V_{CC} DATA RETENTION WAVEFORM**

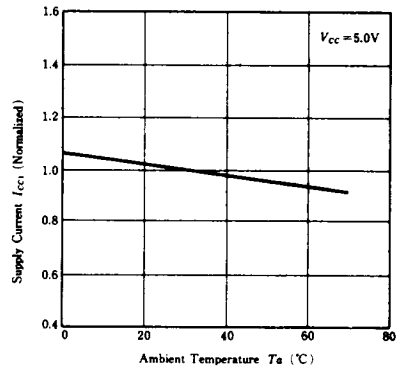


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SUPPLY CURRENT vs. SUPPLY VOLTAGE

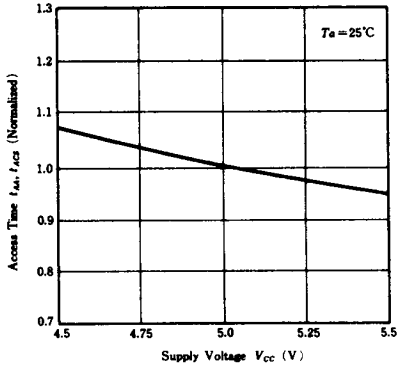


SUPPLY CURRENT vs. AMBIENT TEMPERATURE

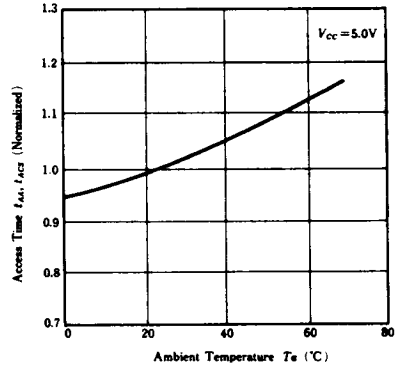


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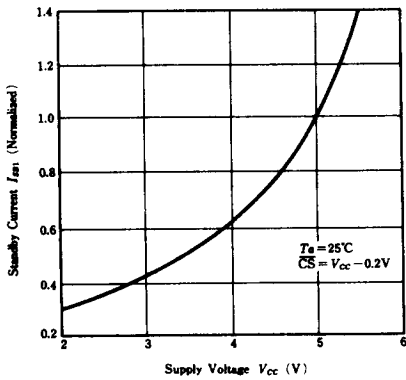
ACCESS TIME vs. SUPPLY VOLTAGE



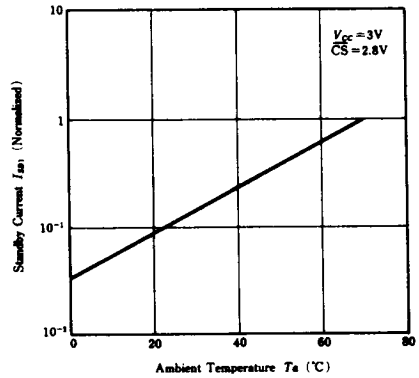
ACCESS TIME vs. AMBIENT TEMPERATURE



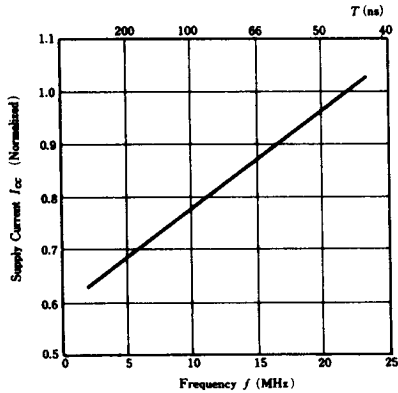
STANDBY CURRENT vs. SUPPLY VOLTAGE



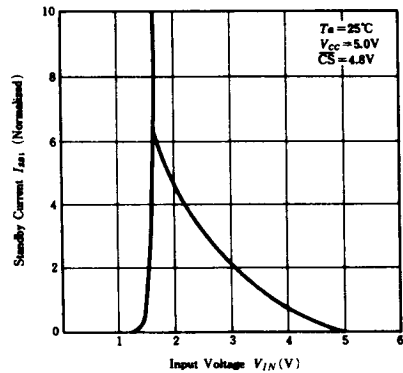
STANDBY CURRENT vs. AMBIENT TEMPERATURE



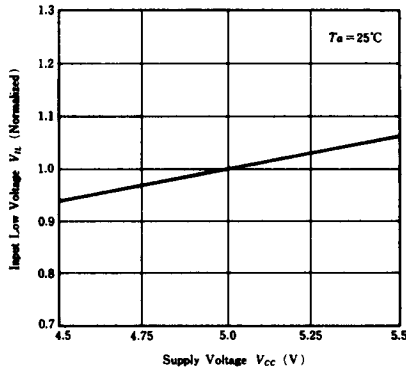
SUPPLY CURRENT vs. FREQUENCY



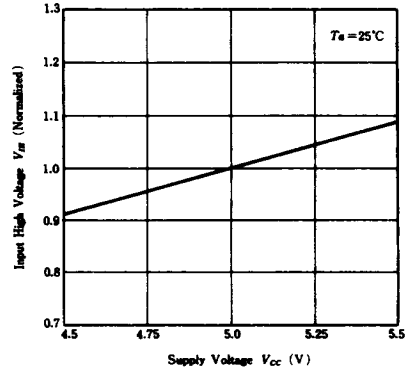
STANDBY CURRENT vs. INPUT VOLTAGE



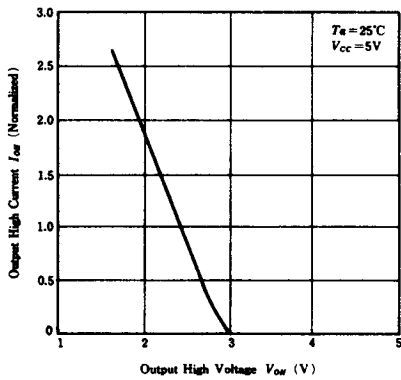
INPUT LOW VOLTAGE vs. SUPPLY VOLTAGE



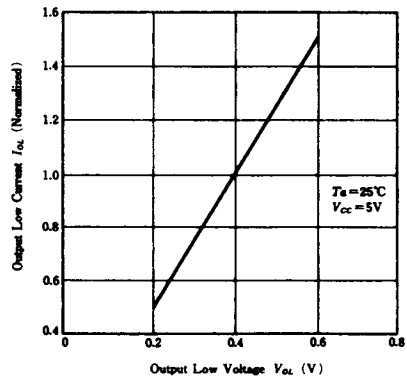
INPUT HIGH VOLTAGE vs. SUPPLY VOLTAGE



OUTPUT HIGH CURRENT vs. OUTPUT HIGH VOLTAGE



OUTPUT LOW CURRENT vs. OUTPUT LOW VOLTAGE



2

